

STRUCTURE AND METHOD OF PATTERNING A MAGNETIC TUNNEL JUNCTION STACK FOR A MAGNETO-RESISTIVE RANDOM ACCESS MEMORY

Abstract

A method of patterning a magnetic tunnel junction (MTJ) stack is provided. According to such method, an MTJ stack is formed having a free layer, a pinned layer and a tunnel barrier layer disposed between the free layer and the pinned layer. A first area of the MTJ stack is masked while the free layer of the MTJ is exposed in a second area. The free layer is then rendered electrically and magnetically inactive in the second area.